

ABSTRACT

Affords ceramic susceptors, for semiconductor manufacturing equipment, in which wafer-surface isothermal quality during heating operations is 5 heightened by enhancing the degree of planarization of the susceptor wafer-carrying face in its high-temperature region where wafers are processed in the course of manufacturing semiconductors.

Ceramic susceptor 1 for semiconductor manufacturing equipment has in the surface or interior of ceramic substrates 2a and 2b resistive heating element 10 3, and a non-heating (ordinary-temperature) arched contour in its wafer-carrying face is a concavity of 0.001 to 0.7 mm per 300 mm. A plasma electrode furthermore may be disposed in ceramic susceptor 1, in the surface or interior of ceramic substrates 2a and 2b. Preferably, moreover, ceramic substrates 2a and 2b are at least one ceramic selected from aluminum nitride, 15 silicon nitride, aluminum oxynitride, and silicon carbide.